RECOMMEND
YJGD60G04HHQ
FOR NEW DESIGN

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

NMOS(Die1/Die2)

ǒ V_{DS}	40V
ǒ I_D	

√ **Ordering Information** (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJGD60G04HJQ	F1					

Typical Electrical and Thermal Characteristics Diagrams

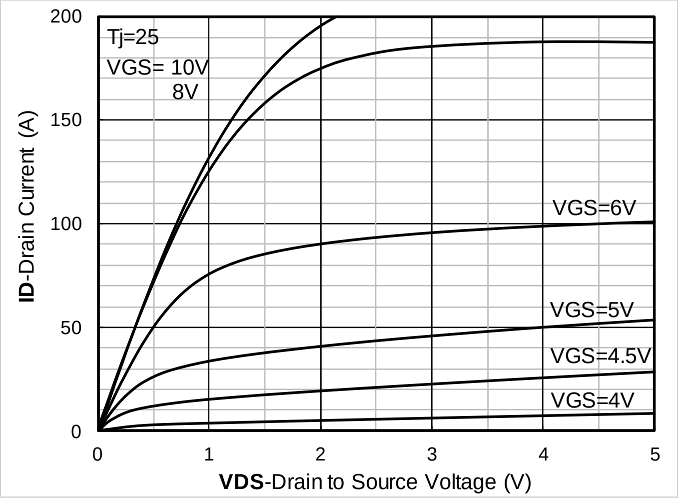


Figure 1. Output Characteristics

Figure 2. Transfer Characteristics

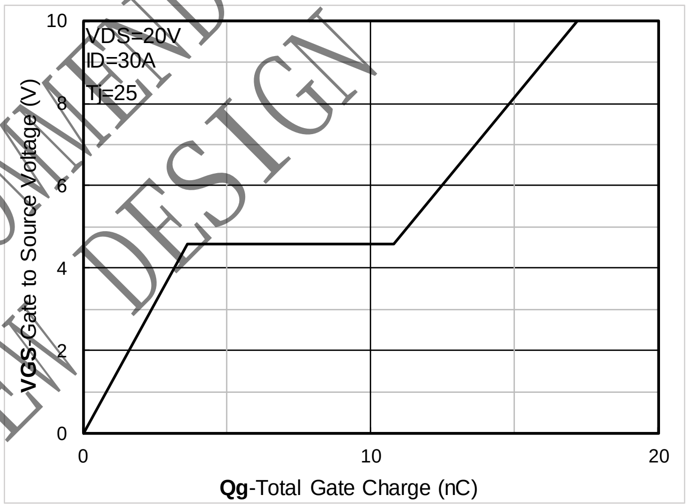
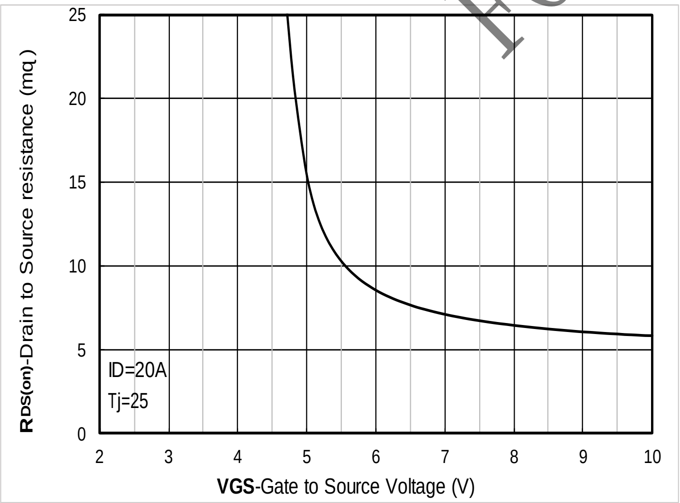


Figure 3. Capacitance Characteristics

Figure 4. Gate Charge



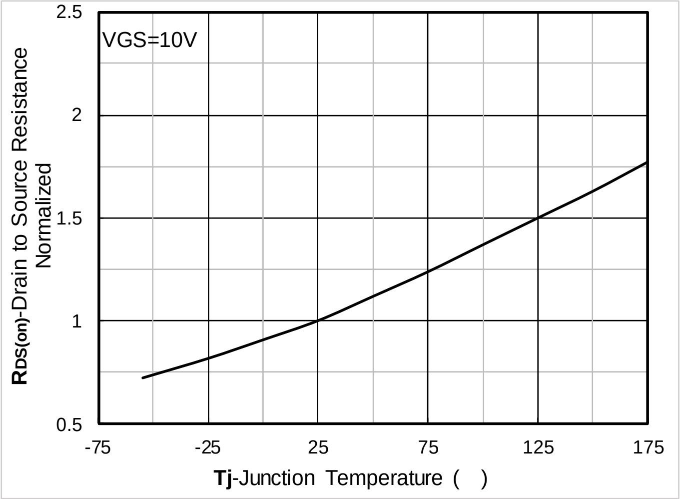


Figure 5. On-Resistance vs Gate to Source Voltage

Figure 6. Normalized On-Resistance

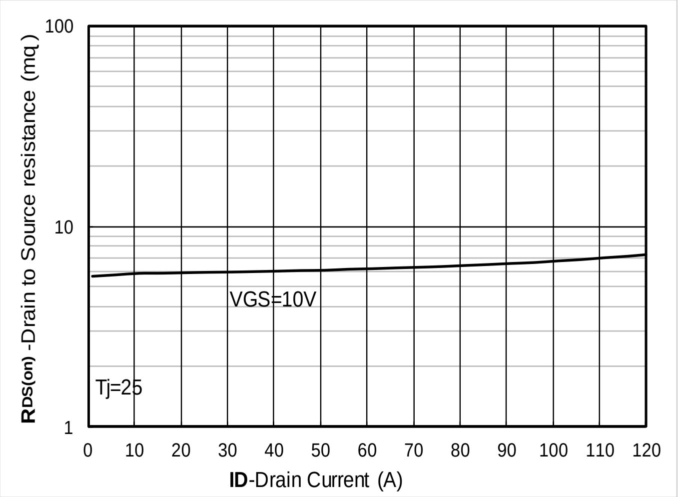


Figure 7. RDS(on) VS Drain Current

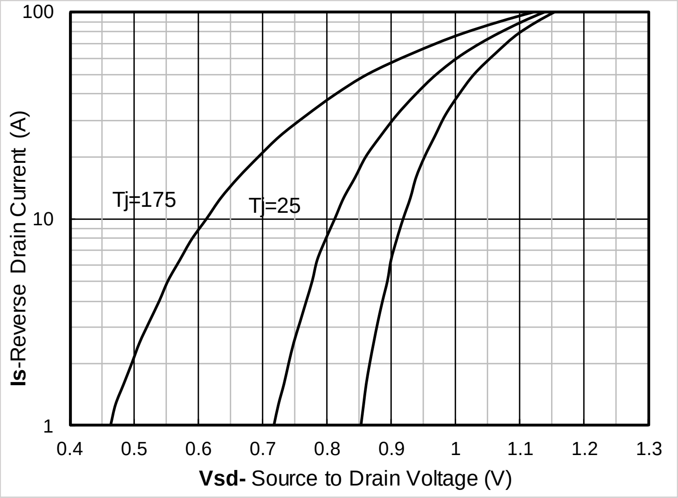


Figure 8. Forward characteristics of reverse diode

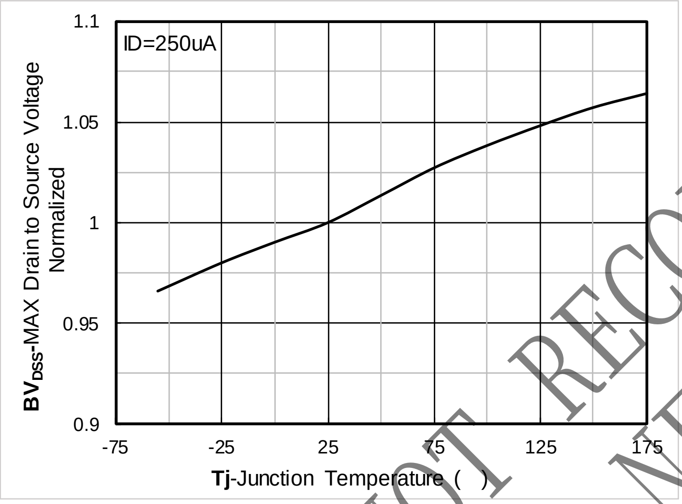


Figure 9. Normalized breakdown voltage

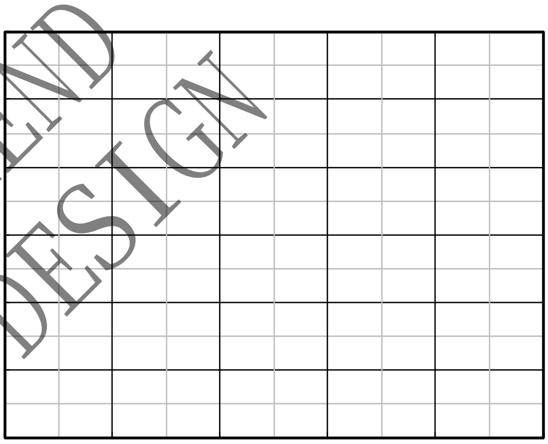


Figure 10. Normalized Threshold voltage

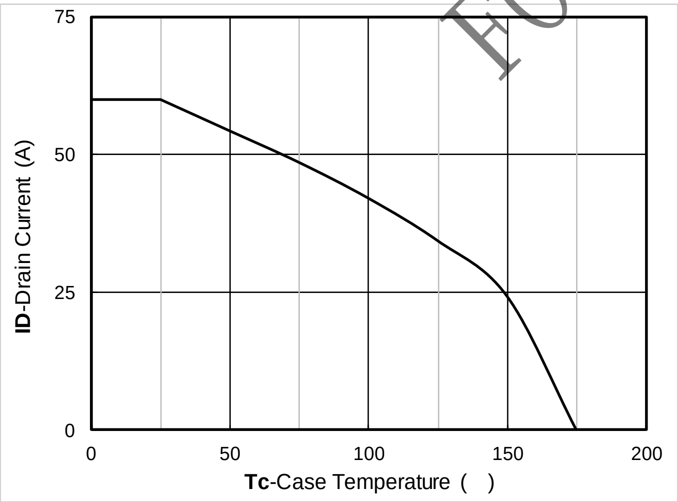


Figure 11. Current dissipation

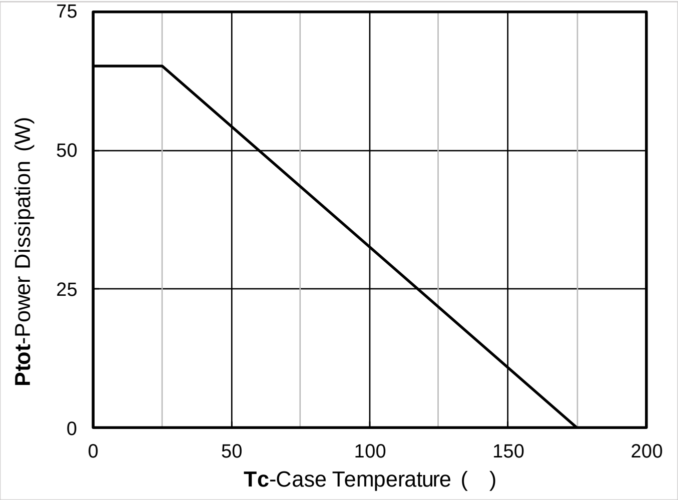


Figure 12. Power dissipation

Figure 13. Maximum Transient Thermal Impedance

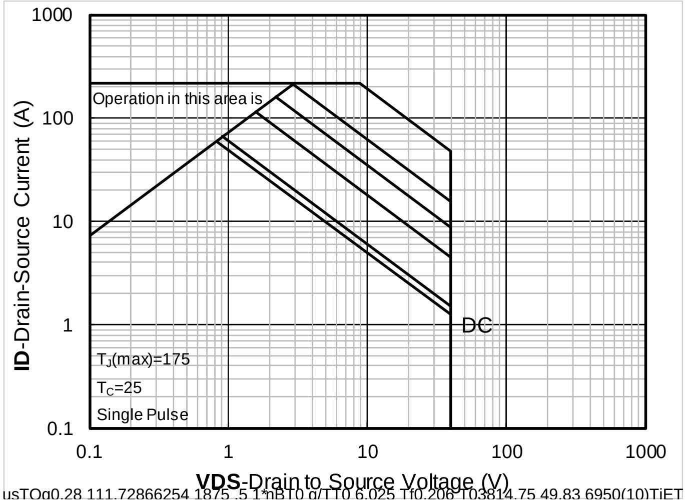


Figure 14. Safe Operation Area